

■ PRODUCT CHARACTERISTICS

VDSS	80V
$R_{DS(on)Typ}(V_{GS}@=10V)$	0.7mΩ
ID	500A

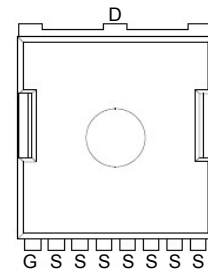
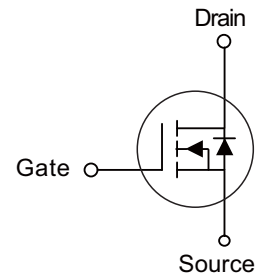
■ APPLICATIONS

- High power system inverter
- Light electric vehicles
- BMS
- Drones

■ FEATURES

- Surface-mounted package
- Advanced trench cell design
- Super trench

Symbol



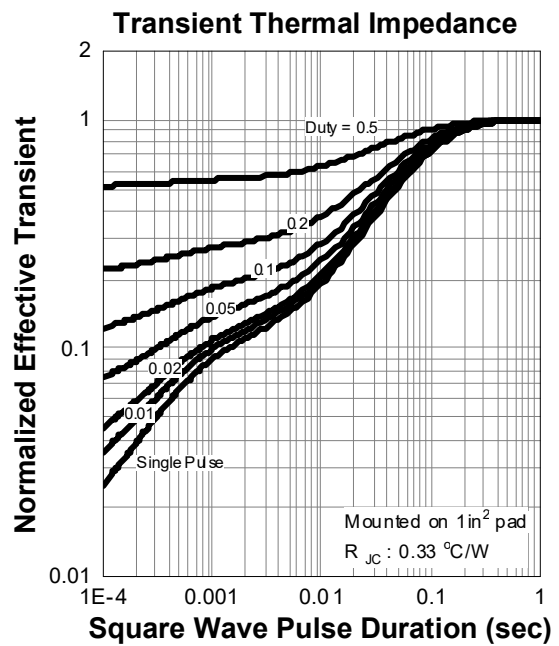
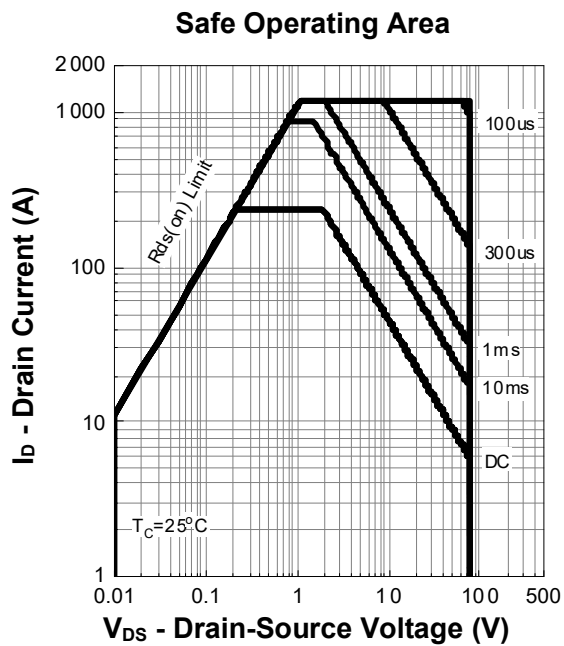
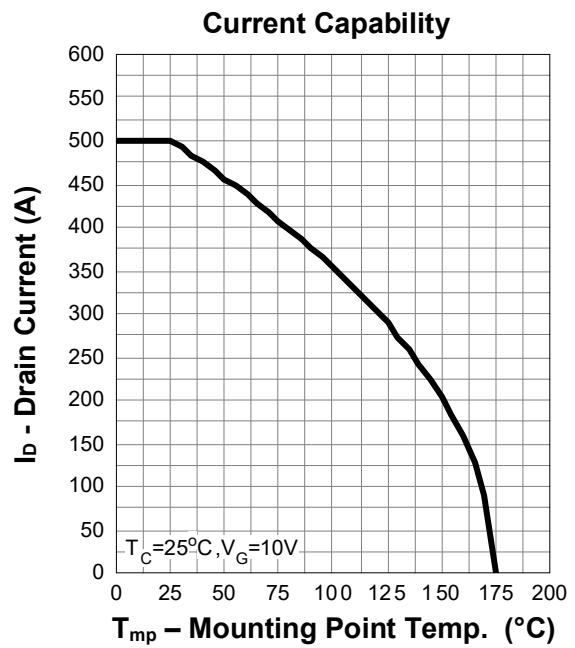
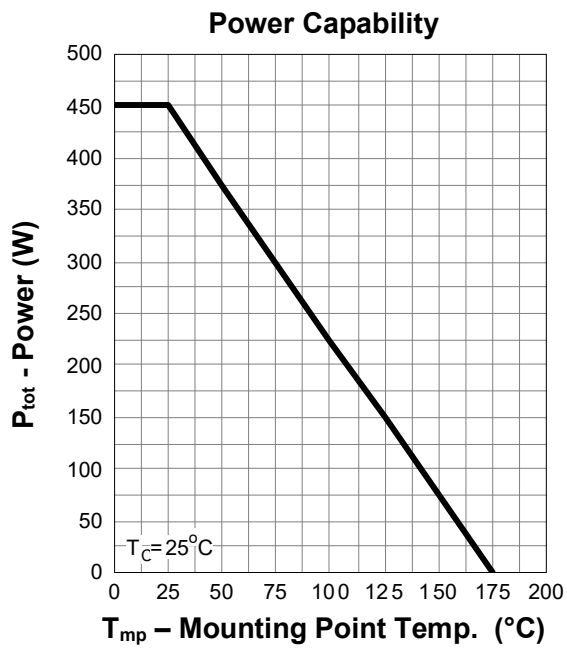
■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Unit
Drain-Source Voltage	V_{DS}	$T_C = 25^\circ\text{C}$	80	-	V
Gate-Source Voltage	V_{GS}	$T_C = 25^\circ\text{C}$	-	± 20	V
Drain Current (DC)	I_D	$T_C = 25^\circ\text{C}, V_{GS} = 10\text{V}$	-	500	A
		$T_C = 100^\circ\text{C}, V_{GS} = 10\text{V}$	-	355	A
Drain Current (Pulsed)	I_{DM}	$T_C = 25^\circ\text{C}, V_{GS} = 10\text{V}$	-	1200	A
Drain power dissipation	P_{tot}	$T_C = 25^\circ\text{C}$	-	450	W
Storage Temperature	T_{stg}		- 55	175	$^\circ\text{C}$
Junction Temperature	T_J		-	175	$^\circ\text{C}$
Continuous-Source Current	I_S	$T_C = 25^\circ\text{C}$	-	500	A
Single Pulsed Avalanche Energy	E_{AS}	$V_{DD} = 50\text{V}, L = 1.0\text{mH}$	-	3042	mJ
Thermal Resistance- Junction to Ambient	$R_{\theta JA}$		-	40	$^\circ\text{C/W}$
Thermal Resistance- Junction to Case	$R_{\theta JC}$		-	0.33	

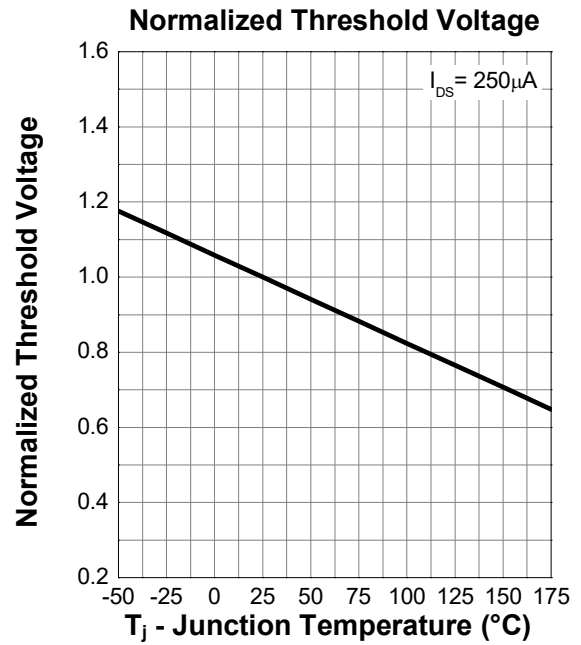
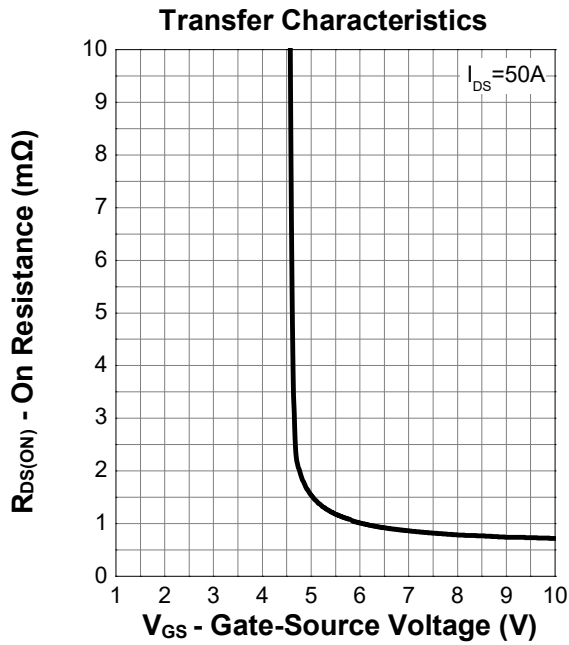
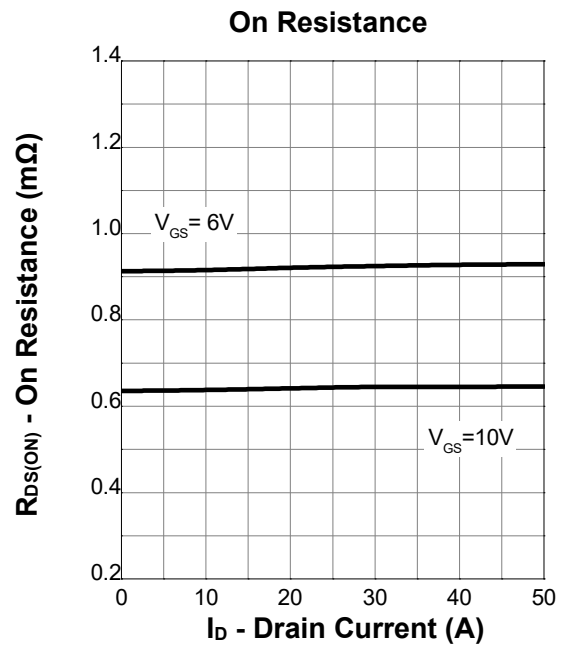
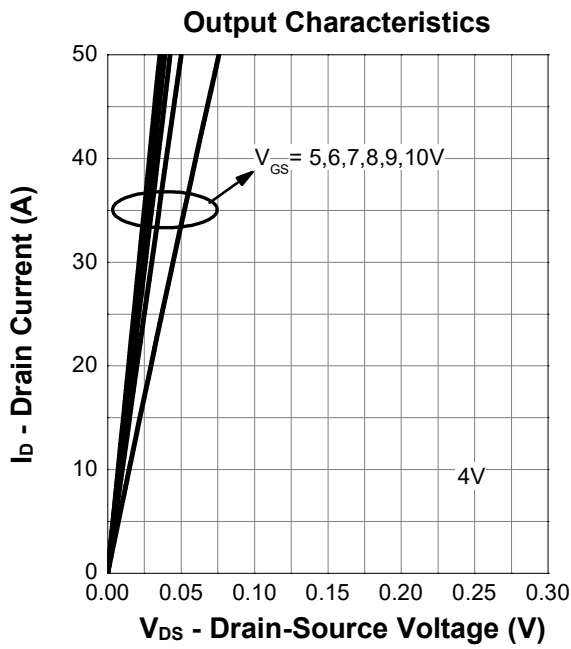
■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{ V}$, $I_{DS} = 250\ \mu\text{A}$	80	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_{DS} = 250\ \mu\text{A}$	2	-	4	V
Drain Leakage Current	I_{DSS}	$V_{DS} = 64\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	1	μA
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$	-	-	± 100	nA
On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_{DS} = 50\text{ A}$	-	0.7	0.85	$\text{m}\Omega$
		$V_{GS} = 6\text{ V}$, $I_{DS} = 30\text{ A}$	-	1.1	1.25	$\text{m}\Omega$
Diode Characteristics						
Diode Forward Voltage	V_{SD}	$I_{SD} = 50\text{ A}$, $V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse Recovery Time	t_{rr}	$I_{DS} = 50\text{ A}$, $V_{GS} = 0\text{ V}$ $di_{SD}/dt = 100\text{ A}/\mu\text{s}$	-	137	-	nS
Reverse Recovery Charge	Q_{rr}		-	369	-	nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 40\text{ V}$ Frequency = 1 MHz	-	8237	-	pF
Output Capacitance	C_{oss}		-	1549	-	
Reverse Transfer Capacitance	C_{rss}		-	152	-	
Turn-on Delay Time	$t_d(on)$	$V_{DS} = 40\text{ V}$, $V_{GEN} = 10\text{ V}$, $R_G = 4.5\ \Omega$, $R_L = 1.3\ \Omega$, $I_{DS} = 30\text{ A}$	-	32	-	nS
Turn-on Rise Time	t_r		-	115	-	
Turn-off Delay Time	$t_d(off)$		-	93	-	
Turn-off Fall Time	t_f		-	140	-	
Gate Charge Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 40\text{ V}$, $V_{GS} = 10\text{ V}$, $I_{DS} = 30\text{ A}$	-	138	-	nC
Gate-Source Charge	Q_{gs}		-	39	-	
Gate-Drain Charge	Q_{gd}		-	36	-	

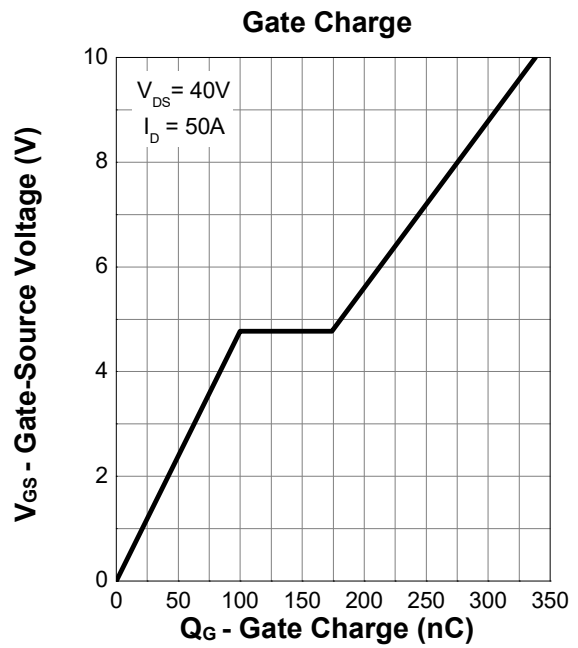
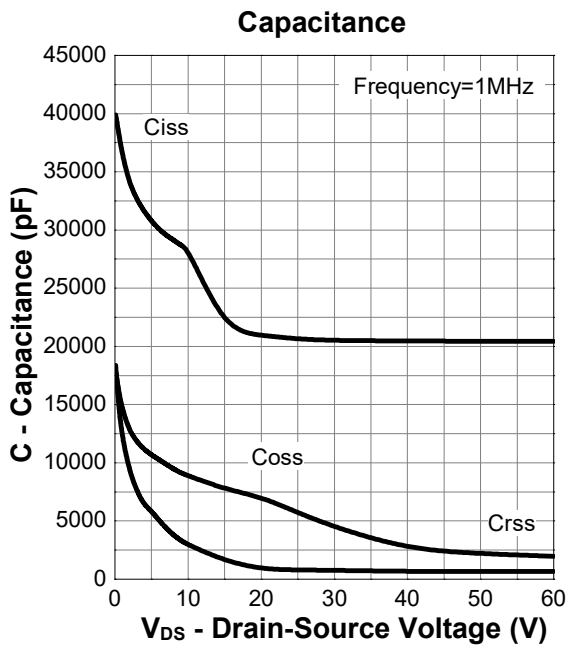
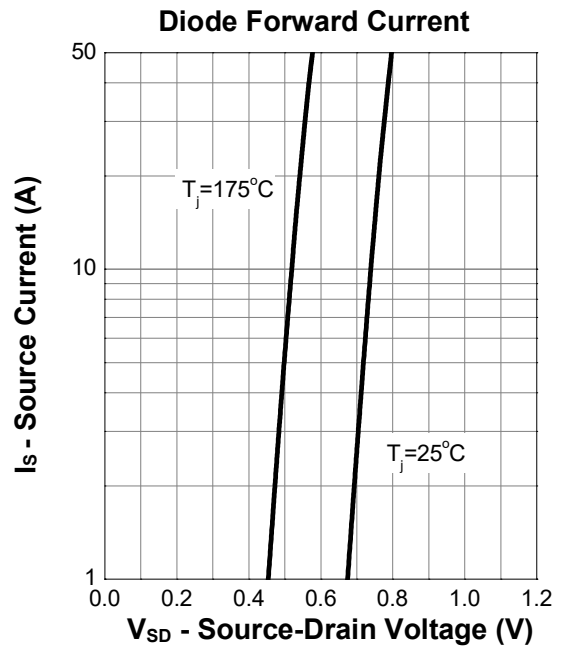
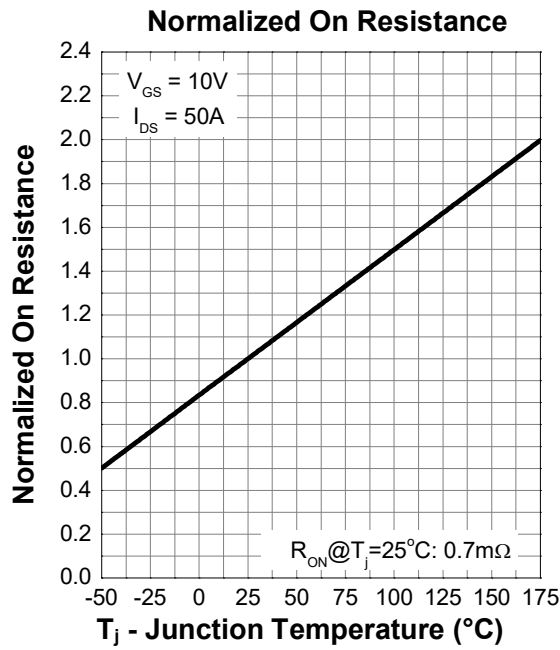
■ TYPICAL CHARACTERISTICS



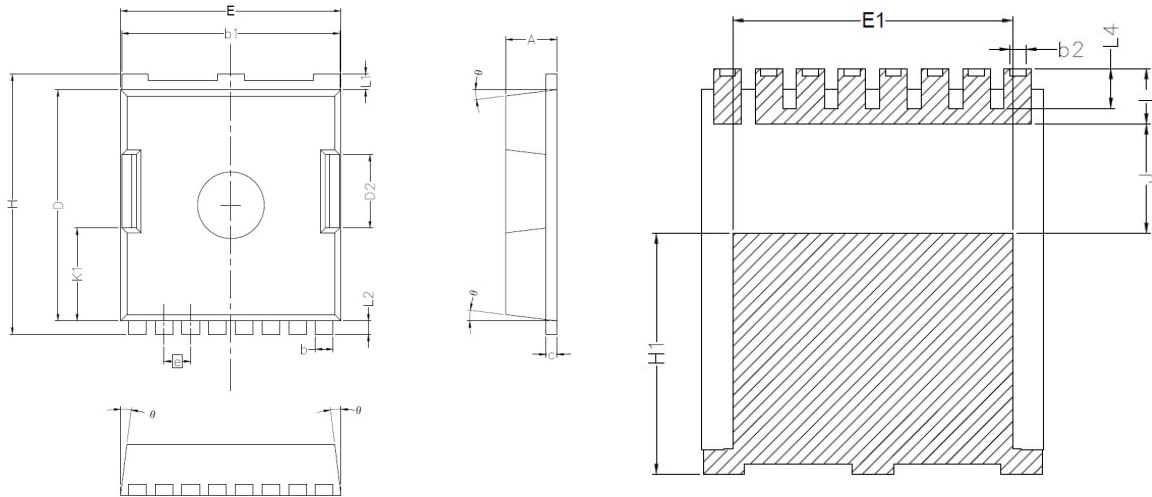
■ TYPICAL CHARACTERISTICS(Cont.)



■ TYPICAL CHARACTERISTICS(Cont.)



■ TOLL-8L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.70	10.10
E1	7.90	8.30
e	1.20BSC	
H	11.48	11.88
H1	6.75	7.15
N	8	
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4	1.00	1.30
θ	4°	10°